RoHS
Available on commercial versions

N-CHANNEL MOSFET

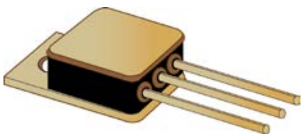
Qualified per MIL-PRF-19500/543

Qualified Levels:
JAN, JANTX, and JANTXV

DESCRIPTION

This family of 2N6764T1, 2N6766T1, 2N6768T1 and 2N6770T1 switching transistors are military qualified up to the JANTXV level for high-reliability applications. These devices are also available in a thru hole TO-204AE metal can package. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website http://www.microsemi.com.



TO-254AA Package

FEATURES

- JEDEC registered 2N6764, 2N6766, 2N6768 and 2N6770 number series.
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/543. (See part nomenclature for all available options.)
- RoHS compliant versions available (commercial grade only).

Also available in:

TO-204AE (TO-3) package
(leaded)
2N6764 & 2N6770

APPLICATIONS / BENEFITS

- Low-profile design.
- Military and other high-reliability applications.

MAXIMUM RATINGS @ T_A = +25 ºC unless otherwise stated

Parameters / Test Conditions		Symbol	Value	Unit
Junction & Storage Temperature Range		T_J & T_{stg}	-55 to +150	°C
Thermal Resistance Junction-to-Case		$R_{ΘJC}$	0.83	°C/W
Total Power Dissipation	@ T_A = +25 °C @ T_C = +25 °C (1)	P_T	4 150	W
Drain-Source Voltage, dc	2N6764T1 2N6766T1 2N6768T1 2N6770T1	V_{DS}	100 200 400 500	V
Gate-Source Voltage, dc		V_{GS}	± 20	V
Drain Current, dc @ T_C = +25 ºC (2)	2N6764T1 2N6766T1 2N6768T1 2N6770T1	I_{D1}	38.0 30.0 14.0 12.0	A
Drain Current, dc @ T_C = +100 ºC (2)	2N6764T1 2N6766T1 2N6768T1 2N6770T1	I_{D2}	24.0 19.0 9.0 7.75	A
Off-State Current (Peak Total Value) (3)	2N6764T1 2N6766T1 2N6768T1 2N6770T1	I_{DM}	152 120 56 48	A (pk)
Source Current	2N6764T1 2N6766T1 2N6768T1 2N6770T1	I_S	38.0 30.0 14.0 12.0	A

Notes featured on next page.

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NOTES:

1. Derate linearly by 1.2 W/ºC for T_C > +25 ºC.
2. The following formula derives the maximum theoretical I_D limit. I_D is limited by package and internal wires and may also be limited by pin diameter:

$$I_D = \sqrt{\frac{T_J\,(max) - T_C}{R_{\theta JC} \times R_{DS(on)} \; @ \; T_J\,(max)}}$$

3. $I_{DM} = 4 \times I_{D1}$ as calculated in note 2.

MECHANICAL and PACKAGING

- CASE: Nickel plated, hermetically sealed, TO-254AA.
- TERMINALS: Ni plated, copper cored, kovar.
- MARKING: Manufacturers ID, part number, date code, Beo (Beryllium Oxide).
- WEIGHT: 6.5 grams.
- See Package Dimensions on last page.

PART NOMENCLATURE

JAN 2N6764 T1 (e3)

Reliability Level
JAN = JAN Level
JANTX = JANTX Level
JANTXV = JANTXV Level
Blank = Commercial

JEDEC type number
(see Electrical Characteristics table)

RoHS Compliance
e3 = RoHS compliant (available on commercial grade only)
Blank = non-RoHS compliant

TO-254AA Package

SYMBOLS & DEFINITIONS

Symbol	Definition
di/dt	Rate of change of diode current while in reverse-recovery mode, recorded as maximum value.
I_F	Forward current
R_G	Gate drive impedance
V_{DD}	Drain supply voltage
V_{DS}	Drain source voltage, dc
V_{GS}	Gate source voltage, dc

ELECTRICAL CHARACTERISTICS @ T_A = +25 °C, unless otherwise noted

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage V_{GS} = 0 V, I_D = 1.0 mA	2N6764T1 2N6766T1 2N6768T1 2N6770T1	$V_{(BR)DSS}$	100 200 400 500		V
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}$, I_D = 0.25 mA $V_{DS} \geq V_{GS}$, I_D = 0.25 mA, T_J = +125 °C $V_{DS} \geq V_{GS}$, I_D = 0.25 mA, T_J = -55 °C		$V_{GS(th)1}$ $V_{GS(th)2}$ $V_{GS(th)3}$	2.0 1.0	4.0 5.0	V
Gate Current V_{GS} = ± 20 V, V_{DS} = 0 V V_{GS} = ± 20 V, V_{DS} = 0 V, T_J = +125 °C		I_{GSS1} I_{GSS2}		±100 ±200	nA
Drain Current V_{GS} = 0 V, V_{DS} = 80 V V_{GS} = 0 V, V_{DS} = 160 V V_{GS} = 0 V, V_{DS} = 320 V V_{GS} = 0 V, V_{DS} = 400 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	I_{DSS1}		25	µA
Drain Current V_{GS} = 0 V, V_{DS} = 100 V, T_J = +125 °C V_{GS} = 0 V, V_{DS} = 200 V, T_J = +125 °C V_{GS} = 0 V, V_{DS} = 400 V, T_J = +125 °C V_{GS} = 0 V, V_{DS} = 500 V, T_J = +125 °C	2N6764T1 2N6766T1 2N6768T1 2N6770T1	I_{DSS2}		1.0	mA
Drain Current V_{GS} = 0 V, V_{DS} = 80 V, T_J = +125 °C V_{GS} = 0 V, V_{DS} = 160 V, T_J = +125 °C V_{GS} = 0 V, V_{DS} = 320 V, T_J = +125 °C V_{GS} = 0 V, V_{DS} = 400 V, T_J = +125 °C	2N6764T1 2N6766T1 2N6768T1 2N6770T1	I_{DSS3}		0.25	mA
Static Drain-Source On-State Resistance V_{GS} = 10 V, I_D = 24.0 A pulsed V_{GS} = 10 V, I_D = 19.0 A pulsed V_{GS} = 10 V, I_D = 9.0 A pulsed V_{GS} = 10 V, I_D = 7.75 A pulsed	2N6764T1 2N6766T1 2N6768T1 2N6770T1	$r_{DS(on)1}$		0.055 0.085 0.3 0.4	Ω
Static Drain-Source On-State Resistance V_{GS} = 10 V, I_D = 38.0 A pulsed V_{GS} = 10 V, I_D = 30.0 A pulsed V_{GS} = 10 V, I_D = 14.0 A pulsed V_{GS} = 10 V, I_D = 12.0 A pulsed	2N6764T1 2N6766T1 2N6768T1 2N6770T1	$r_{DS(on)2}$		0.065 0.09 0.4 0.5	Ω
Static Drain-Source On-State Resistance T_J = +125 °C V_{GS} = 10 V, I_D = 24.0 A pulsed V_{GS} = 10 V, I_D = 19.0 A pulsed V_{GS} = 10 V, I_D = 9.0 A pulsed V_{GS} = 10 V, I_D = 7.75 A pulsed	2N6764T1 2N6766T1 2N6768T1 2N6770T1	$r_{DS(on)3}$		0.094 0.153 0.66 0.88	Ω
Diode Forward Voltage V_{GS} = 0 V, I_D = 38.0 A pulsed V_{GS} = 0 V, I_D = 30.0 A pulsed V_{GS} = 0 V, I_D = 14.0 A pulsed V_{GS} = 0 V, I_D = 12.0 A pulsed	2N6764T1 2N6766T1 2N6768T1 2N6770T1	V_{SD}		1.9 1.9 1.7 1.7	V

ELECTRICAL CHARACTERISTICS @ T_A = +25 °C, unless otherwise noted (continued)

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Gate Charge:					
On-State Gate Charge V_{GS} = 10 V, I_D = 38.0 A, V_{DS} = 50 V V_{GS} = 10 V, I_D = 30.0 A, V_{DS} = 100 V V_{GS} = 10 V, I_D = 14.0 A, V_{DS} = 200 V V_{GS} = 10 V, I_D = 12.0 A, V_{DS} = 250 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	$Q_{g(on)}$		125 115 110 120	nC
Gate to Source Charge V_{GS} = 10 V, I_D = 38.0 A, V_{DS} = 50 V V_{GS} = 10 V, I_D = 30.0 A, V_{DS} = 100 V V_{GS} = 10 V, I_D = 14.0 A, V_{DS} = 200 V V_{GS} = 10 V, I_D = 12.0 A, V_{DS} = 250 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	Q_{gs}		22 22 18 19	nC
Gate to Drain Charge V_{GS} = 10 V, I_D = 38.0 A, V_{DS} = 50 V V_{GS} = 10 V, I_D = 30.0 A, V_{DS} = 100 V V_{GS} = 10 V, I_D = 14.0 A, V_{DS} = 200 V V_{GS} = 10 V, I_D = 12.0 A, V_{DS} = 250 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	Q_{gd}		65 60 65 70	nC

SWITCHING CHARACTERISTICS

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Turn-on delay time I_D = 38.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 50 V I_D = 30.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 100 V I_D = 14.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 200 V I_D = 12.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 250 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	$t_{d(on)}$		35	ns
Rise time I_D = 38.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 50 V I_D = 30.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 100 V I_D = 14.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 200 V I_D = 12.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 250 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	t_r		190	ns
Turn-off delay time I_D = 38.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 50 V I_D = 30.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 100 V I_D = 14.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 200 V I_D = 12.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 250 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	$t_{d(off)}$		170	ns
Fall time I_D = 38.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 50 V I_D = 30.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 100 V I_D = 14.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 200 V I_D = 12.0 A, V_{GS} = +10 V, R_G = 2.35 Ω, V_{DD} = 250 V	2N6764T1 2N6766T1 2N6768T1 2N6770T1	t_f		130	ns
Diode Reverse Recovery Time di/dt = 100 A/µs, V_{DD} ≤ 30 V, I_D = 38.0 A di/dt = 100 A/µs, V_{DD} ≤ 30 V, I_D = 30.0 A di/dt = 100 A/µs, V_{DD} ≤ 30 V, I_D = 14.0 A di/dt = 100 A/µs, V_{DD} ≤ 30 V, I_D = 12.0 A	2N6764T1 2N6766T1 2N6768T1 2N6770T1	t_{rr}		500 950 1200 1600	ns

GRAPHS

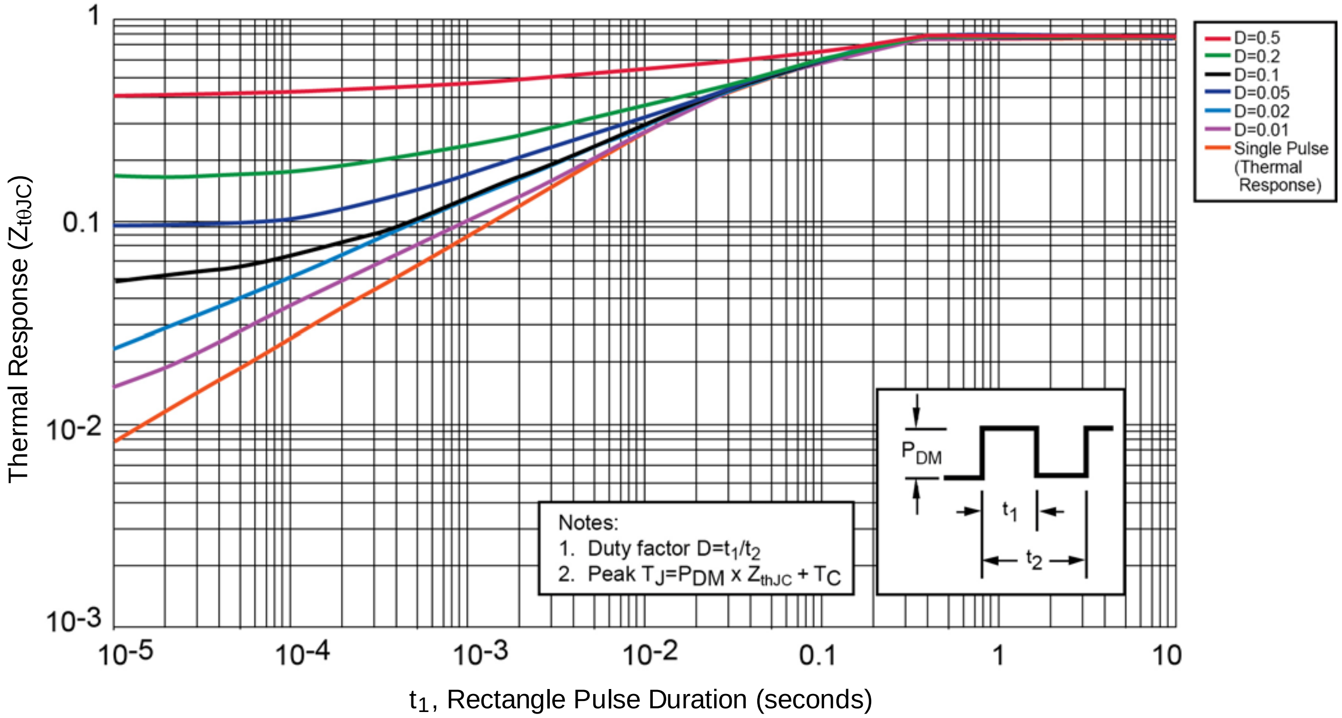
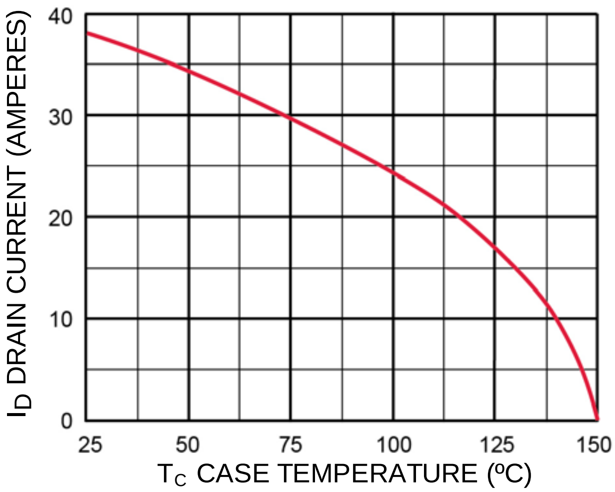


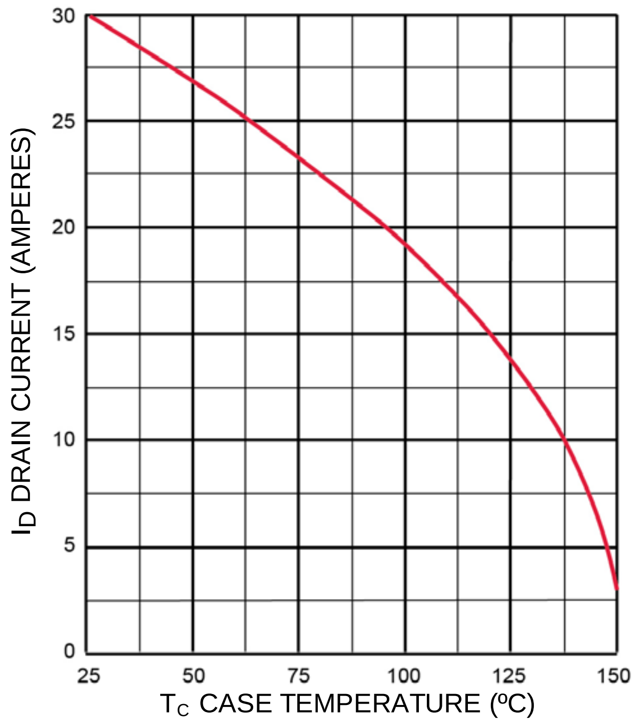
FIGURE 1
Thermal Response Curves

GRAPHS (continued)

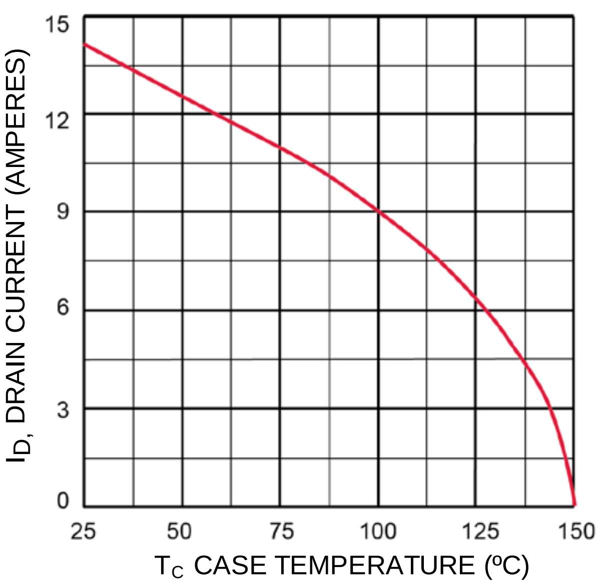
FIGURE 2 – Maximum Drain Current vs Case Temperature Graphs



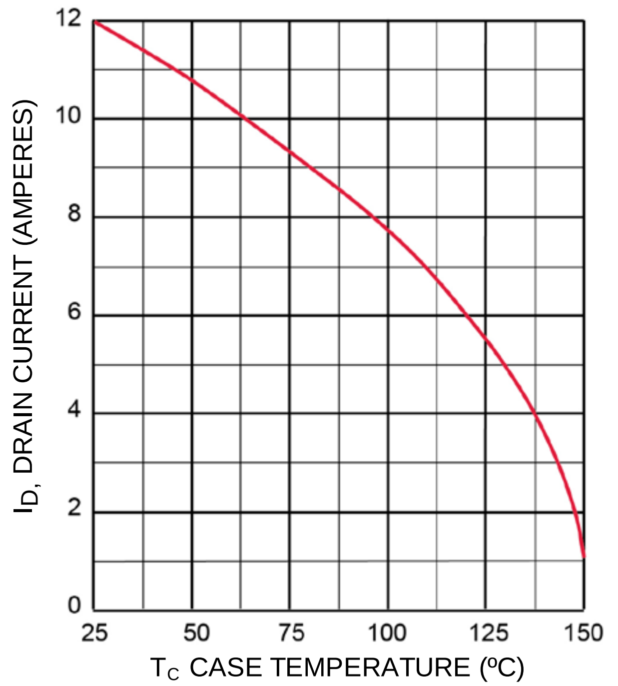
For 2N6764T1



For 2N6766T1



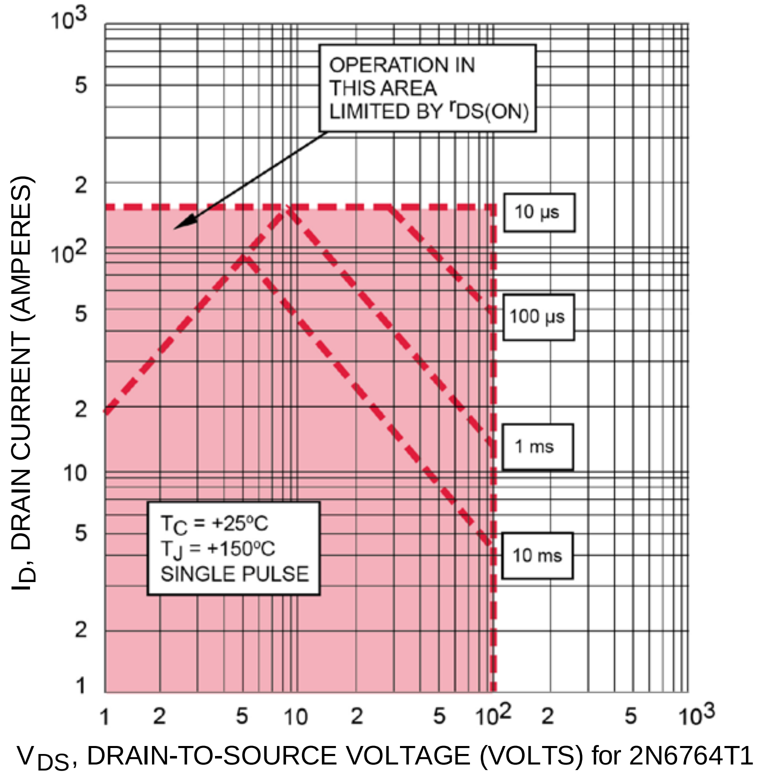
For 2N6768T1

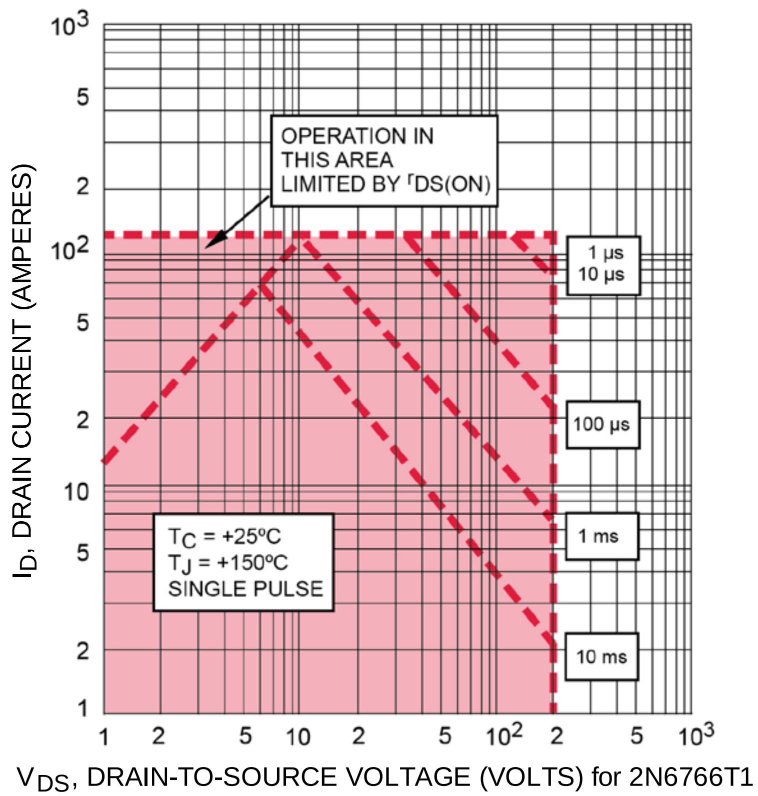


For 2N6770T1

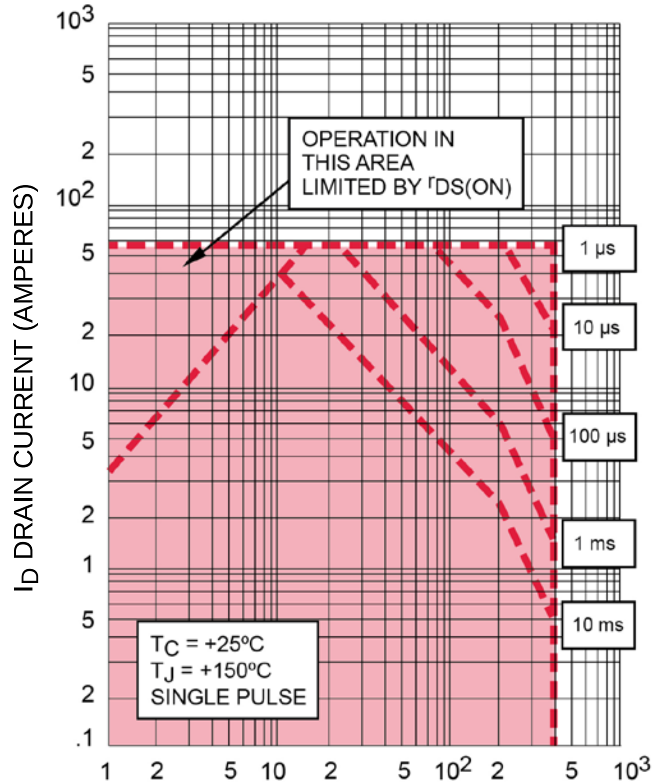
GRAPHS (continued)

FIGURE 3 – Maximum Safe Operating Area

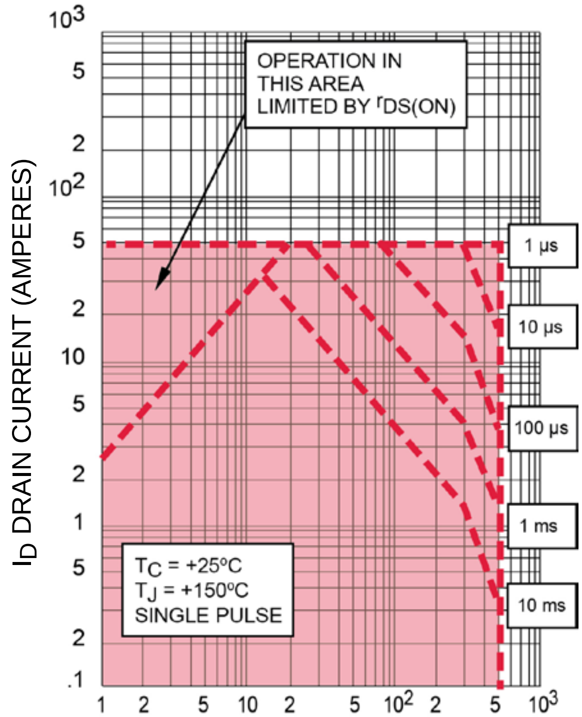




GRAPHS (continued)

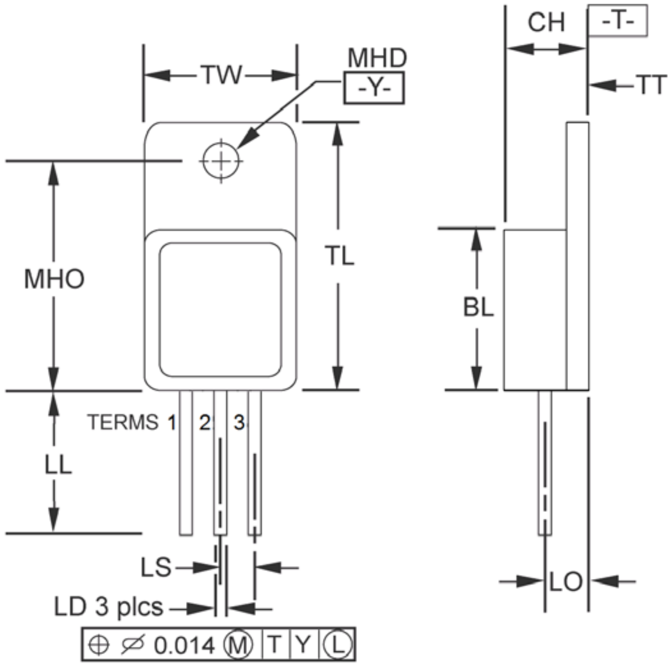


V_{DS}, DRAIN-TO-SOURCE VOLTAGE (VOLTS) for 2N6768T1



V_{DS}, DRAIN-TO-SOURCE VOLTAGE (VOLTS) for 2N6770T1

PACKAGE DIMENSIONS



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Protrusion thickness of ceramic eyelets included in dimension LL.
4. All terminals are isolated from case.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

Ltr	Dimensions				Notes
	Inch		Millimeters		
	Min	Max	Min	Max	
BL	0.535	0.545	13.59	13.84	
CH	0.249	0.260	6.32	6.60	
LD	0.035	0.045	0.89	1.14	
LL	0.510	0.570	12.95	14.48	3,4
LO	0.150 BSC		3.81 BSC		
LS	0.150 BSC		3.81 BSC		
MHD	0.139	0.149	3.53	3.78	
MHO	0.665	0.685	16.89	17.40	
TL	0.790	0.800	20.07	20.32	
TT	0.040	0.050	1.02	1.27	
TW	0.535	0.545	13.59	13.84	
Term 1	Drain				
Term 2	Source				
Term 3	Gate				